

SKKT 132 H4, SKKH 132 H4



SEMIPACK[®] 2

Thyristor / Diode Modules

SKKH 132 H4

SKKT 132 H4

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

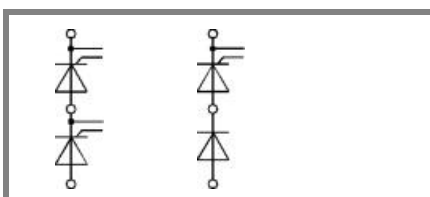
Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 220$ A (maximum value for continuous operation) $I_{TAV} = 132$ A (sin. 180; $T_c = 84$ °C)	
2100	2000	SKKT 132/20E H4	SKKH 132/20E H4
2300	2200	SKKT 132/22E H4	SKKH 132/22E H4

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	128 (90)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 125$ °C; 10 ms	4500 3800	A A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 125$ °C; 8,3 ... 10 ms	100000 72000	A ² s A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 500$ A	max. 1,8	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 1,1	V
r_T	$T_{vj} = 125$ °C	max. 2	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 40	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 200	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
t_q	$T_{vj} = 125$ °C	50 ... 150	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 400	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 1000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,17 / 0,085	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,18 / 0,09	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,2 / 0,1	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminal	5 ± 15 %	Nm
a		$5 * 9,81$	m/s ²
m	approx.	175	g
Case	SKKT SKKH	A 21 A 22	



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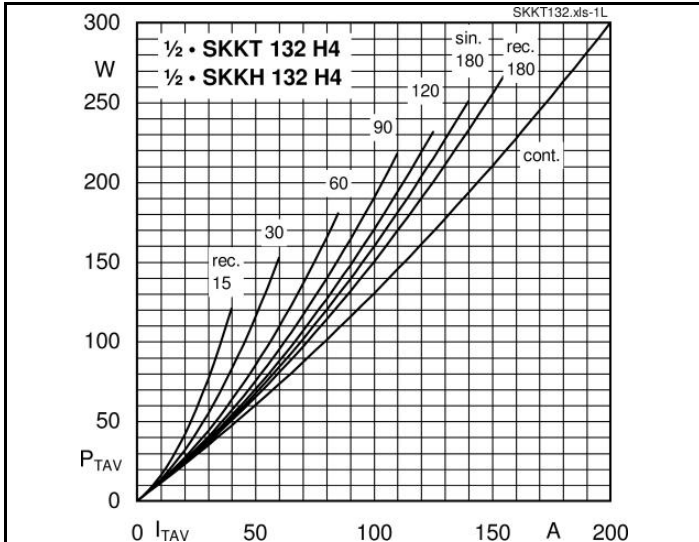


Fig. 1L Power dissipation per thyristor vs. on-state current

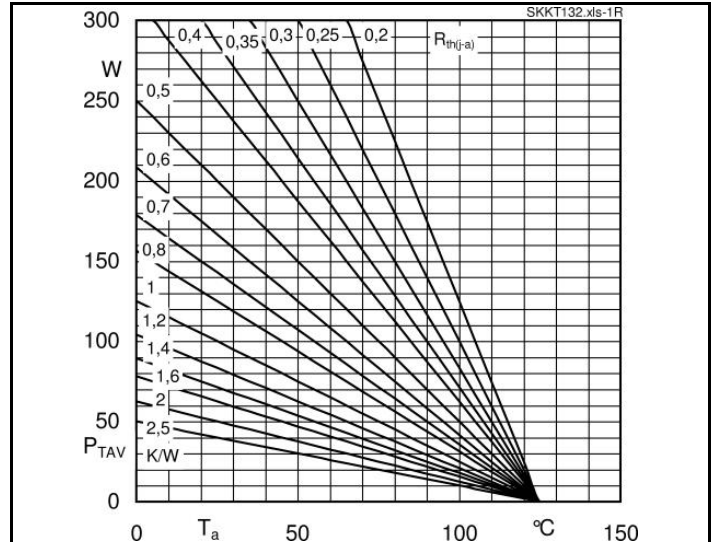


Fig. 1R Power dissipation per thyristor vs. ambient temp.

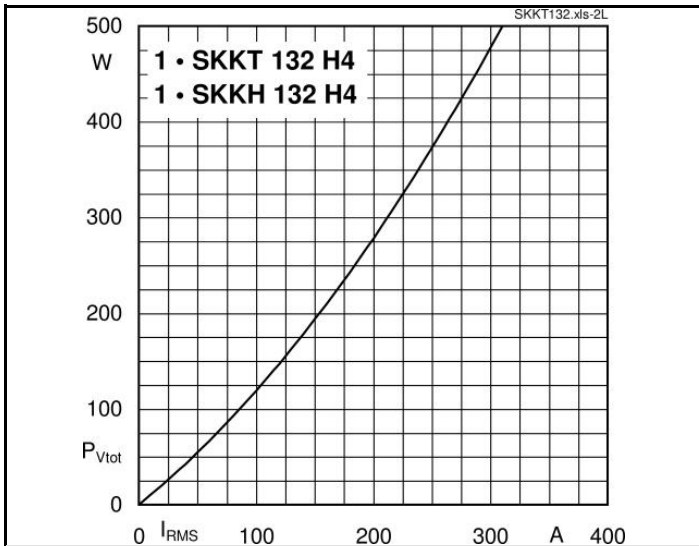


Fig. 2L Power dissipation per module vs. rms current

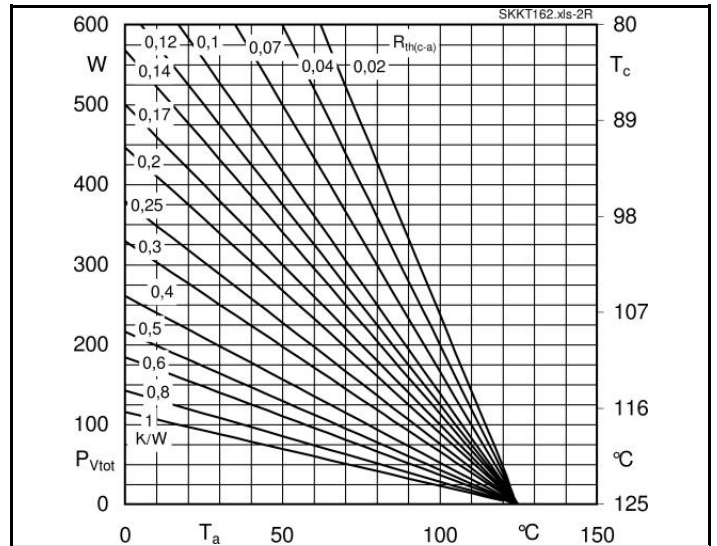


Fig. 2R Power dissipation per module vs. case temp.

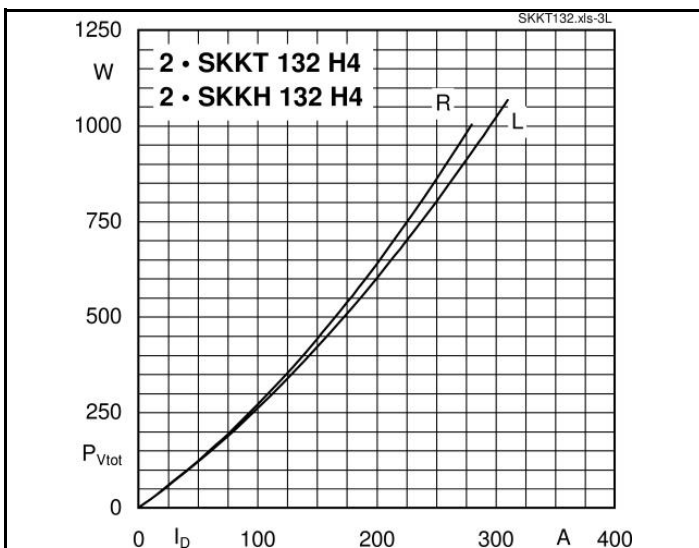


Fig. 3L Power dissipation of two modules vs. direct current

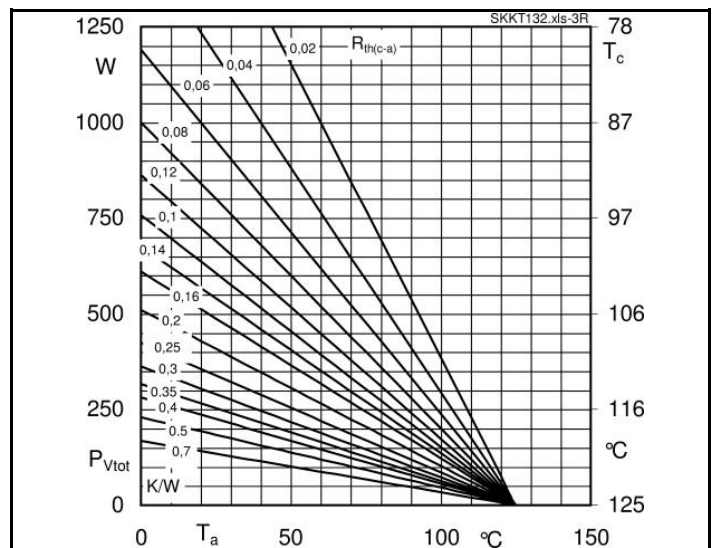
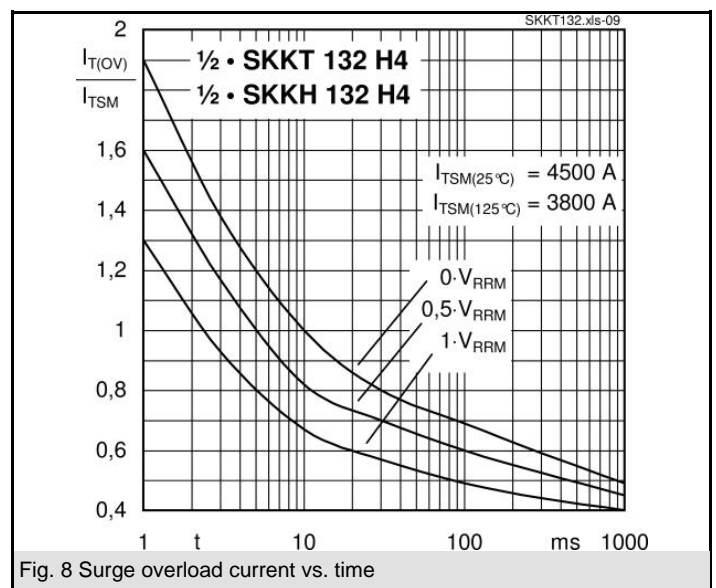
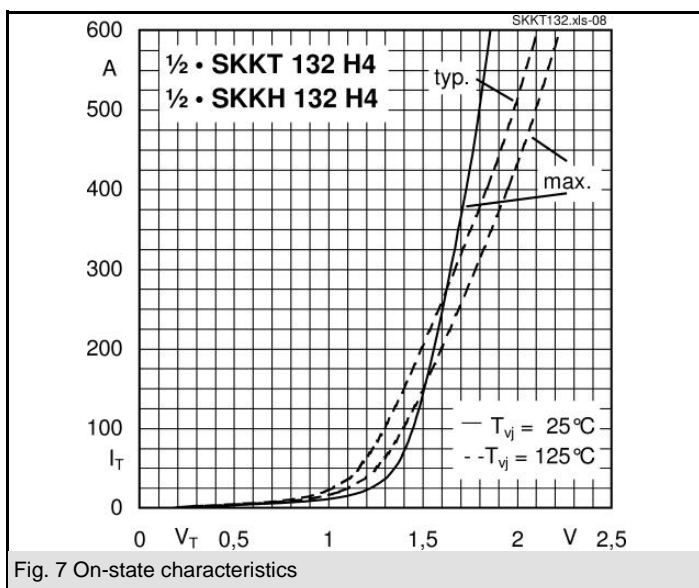
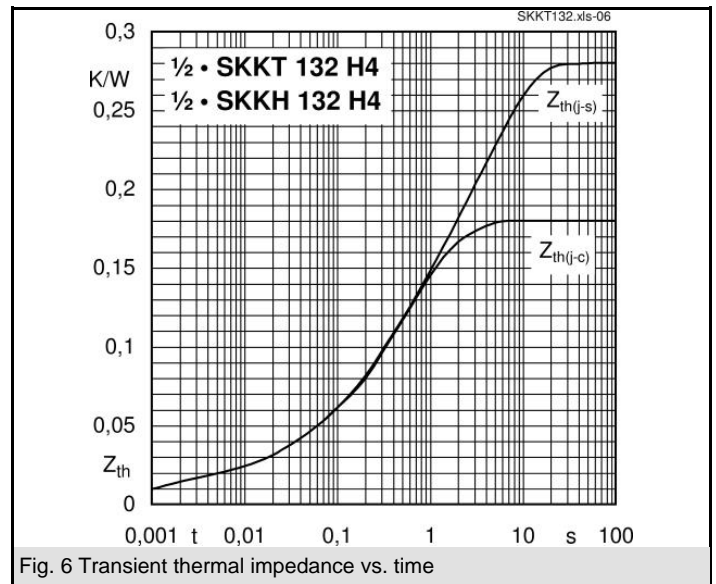
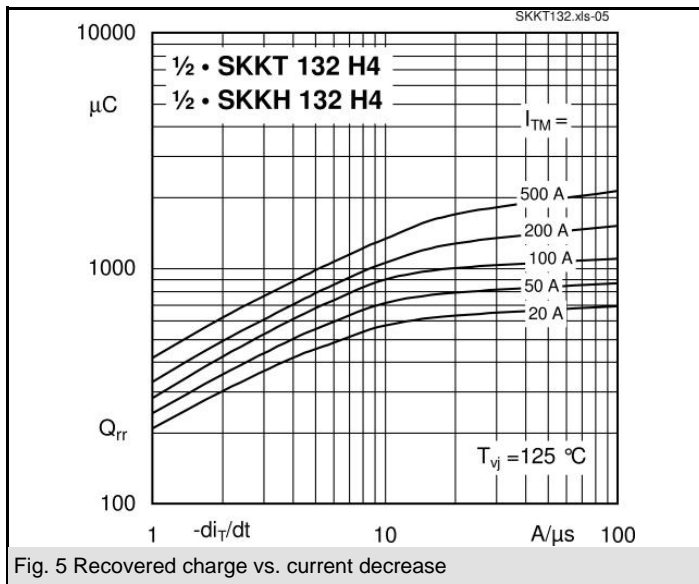
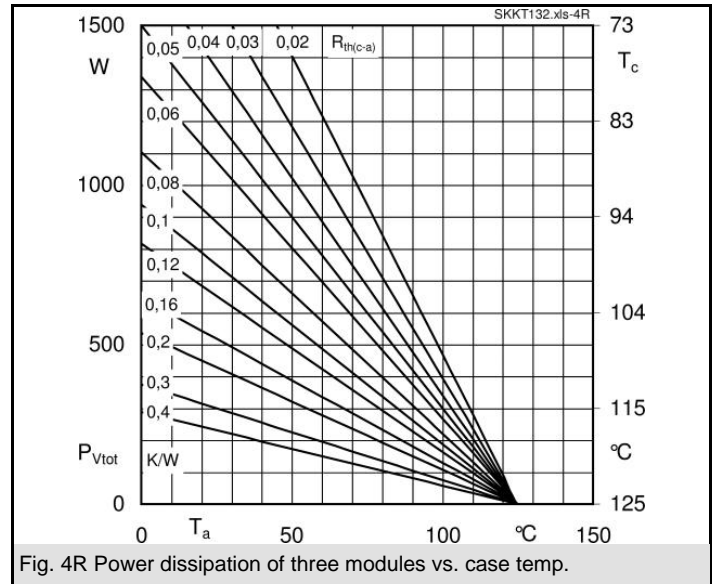
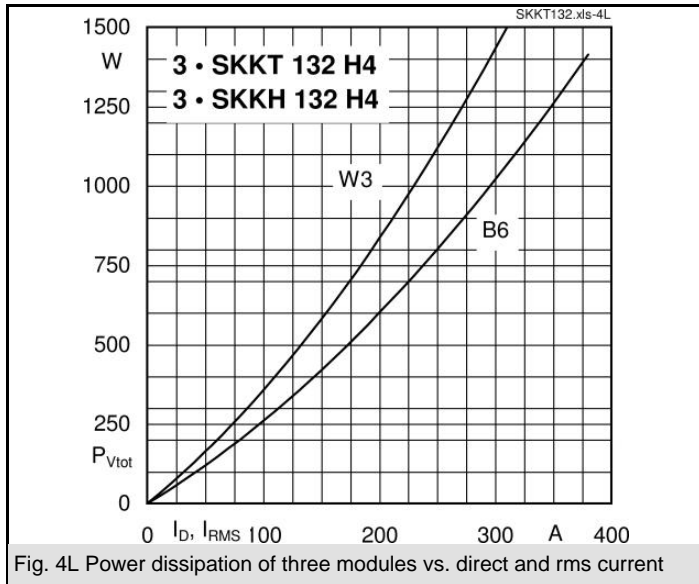
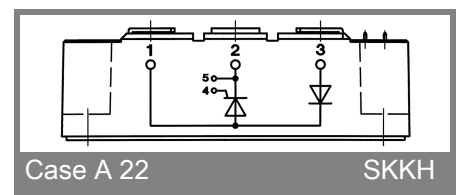
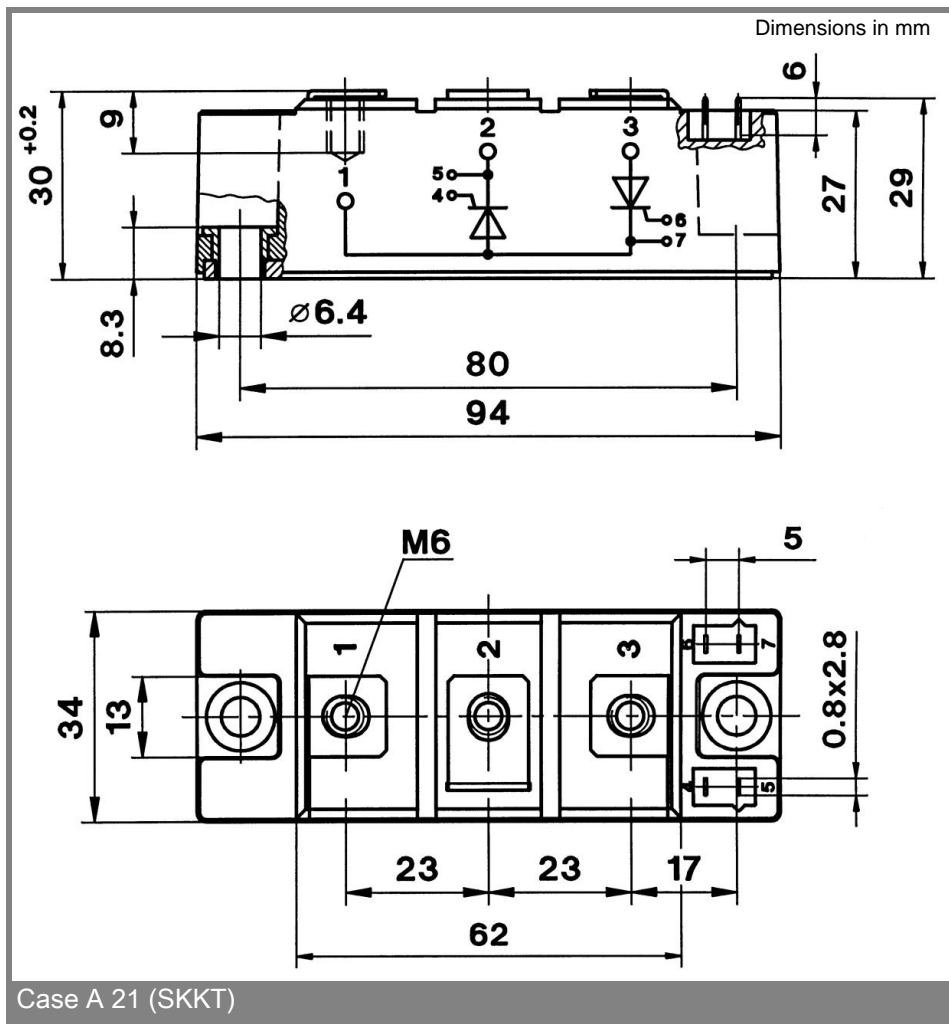
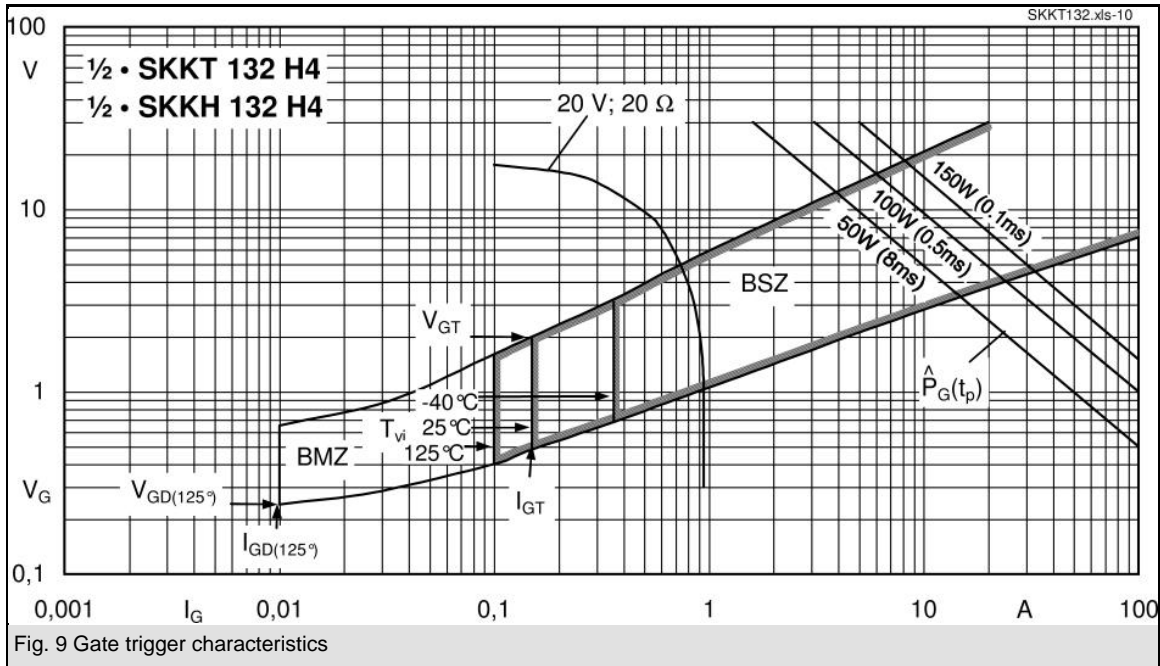


Fig. 3R Power dissipation of two modules vs. case temp.

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